

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	2	((chip IC die) and (dic\$3 singulat\$3 cut\$3 saw\$3) and (cover\$3 laminat\$3 clos\$3) and (protect\$3 insulat\$3 mask\$3) and (inject\$3 near5 mold\$3) and (trench recess groove hole open\$3) and (fill\$3 mold\$3) and (remov\$3 detaching) and conduct\$3 and electrical\$3).clm.	US-PGPU B	OR	ON	2005/09/15 18:33

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	1819041	dic\$3 cut\$3 delaminat\$3	US-PGPU B; USPAT; USOCR	OR	ON	2005/09/15 15:56
L2	301238	1 and mold\$3	US-PGPU B; USPAT; USOCR	OR	ON	2005/09/15 15:57
L3	145554	2 and (insulat\$3 protect\$3)	US-PGPU B; USPAT; USOCR	OR	ON	2005/09/15 15:57
L4	134471	3 and (trench open\$3 hole groove recess contact)	US-PGPU B; USPAT; USOCR	OR	ON	2005/09/15 15:57
L5	38563	4 and (wafer substrate)	US-PGPU B; USPAT; USOCR	OR	ON	2005/09/15 15:23
L6	22362	5 and (die chip IC)	US-PGPU B; USPAT; USOCR	OR	ON	2005/09/15 15:24
L8	815417	dic\$3 cut\$3 delaminat\$3	EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/09/15 15:56
L9	28092	8 and mold\$3	EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/09/15 15:57
L10	2350	9 and (insulat\$3 protect\$3)	EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/09/15 15:57
L11	933	10 and ((trench open\$3 hole groove recess contact))	EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/09/15 16:25
L12	20137	6 and ((contact bump electrode))	US-PGPU B; USPAT; USOCR	OR	ON	2005/09/15 15:59
L13	12347	12 and resin	US-PGPU B; USPAT; USOCR	OR	ON	2005/09/15 16:00

L14	4042	13 and (inject\$3 near5 mold\$3)	US-PGPU B; USPAT; USOCR	OR	ON	2005/09/15 16:01
L15	1417	14 and (dic\$3 saw\$3)	US-PGPU B; USPAT; USOCR	OR	ON	2005/09/15 16:01
L16	60	11 and (dic\$3 saw\$3)	EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/09/15 16:25